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Rose
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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Application Serial No. 09/428,125
Filing Date October 26, 1999
Inventor Vishnu K. Agarwal et al
Assignee Micron Technology, Inc.
Group Art Unit 2822
Examiner Rose, Kiesha L.
Attorney's Docket No. MI22-1299
Title: Capacitors and Methods of Forming Capacitors

RESPONSE TO SEPTEMBER 10, 2002 FINAL OFFICE ACTION
Response to accompany an RCE filing

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To: BOX RCE
Assistant Commissioner for Patents
Washington, D.C. 20231

From: David G. Latwesen, Ph.D. (Tel. 509-624-4276; Fax 509-838-3424)
Wells St. John P.S.
601 W. First Avenue, Suite 1300
Spokane, WA 99201-3828

AMENDMENTS**In the Specification**

Please replace the paragraph beginning at line 3 of page 8 with the following clean replacement paragraph in accordance with 37 C.F.R. § 1.121(b)(1)(ii):

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--Accordingly in the above described preferred embodiment, first layer 18 of the capacitor dielectric layer material is essentially provided with a selected finished crystalline structure prior to formation of second layer 20 thereon. Such is achieved by the crystallization or recrystallization anneal immediately prior to formation of layer 20. Also in the preferred embodiment, the final composition of second layer 20 of the first material is also desirably formed to be crystalline, although alternately such could remain amorphous if so initially deposited. In the preferred embodiment